

# RGTH00TS65

## 650V 50A Field Stop Trench IGBT

$V_{CES}$	650V
I <sub>C(100°C)</sub>	50A
V <sub>CE(sat) (Typ.)</sub>	1.6V
$P_D$	277W

### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

### Applications

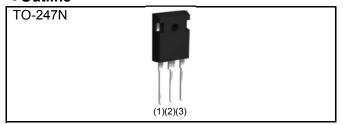
**PFC** 

**UPS** 

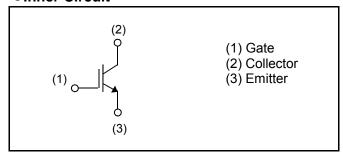
**Power Conditioner** 

ΙH

### Outline



### ●Inner Circuit



### Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing code	C11
	Marking	RGTH00TS65

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit	
Collector - Emitter Voltage		V <sub>CES</sub>	650	V	
Gate - Emitter Voltage		$V_{GES}$	±30	V	
Callactor Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	85	А	
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	50	А	
Pulsed Collector Current		I <sub>CP</sub> *1	200	А	
$T_C = 25^{\circ}C$		P <sub>D</sub>	277	W	
Power Dissipation $T_C = 100^{\circ}C$		P <sub>D</sub>	138	W	
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C	
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C	

<sup>\*1</sup> Pulse width limited by T<sub>imax</sub>.

### ●Thermal Resistance

Parameter	Symbol	Values			Unit
Farameter		Min.	Тур.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.54	°C/W

# ullet IGBT Electrical Characteristics (at $T_j$ = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai i i e te i	Symbol		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	ı	V
Collector Cut - off Current	I <sub>CES</sub>	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	1	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 34.7 \text{mA}$	4.5	5.5	6.5	V
		I <sub>C</sub> = 50A, V <sub>GE</sub> = 15V				
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	T <sub>j</sub> = 25°C	-	1.6	2.1	V
		T <sub>j</sub> = 175°C	-	2.1	-	

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	2740	-	
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> = 0V	-	106	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	43	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>CE</sub> = 300V	-	94	-	
Gate - Emitter Charge	$Q_ge$	I <sub>C</sub> = 50A	-	22	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	31	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 50A, V <sub>CC</sub> = 400V	-	39	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	143	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	50	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 50A, V <sub>CC</sub> = 400V	-	39	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	159	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	62	-	
		I <sub>C</sub> = 200A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

**Data Sheet** RGTH00TS65

### • Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

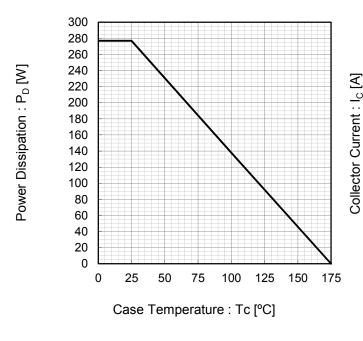
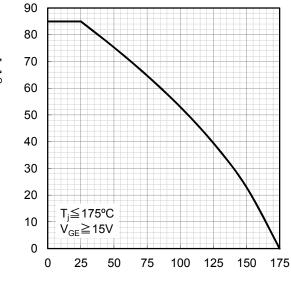
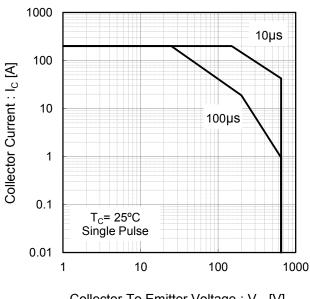


Fig.2 Collector Current vs. Case Temperature



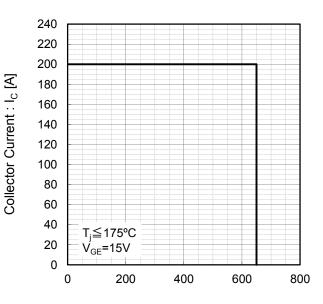
Case Temperature : Tc [°C]

Fig.3 Forward Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

### • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

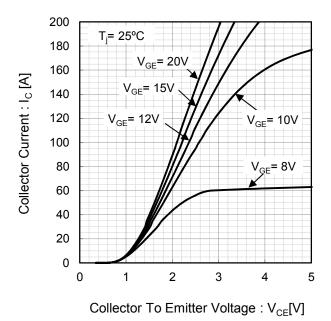
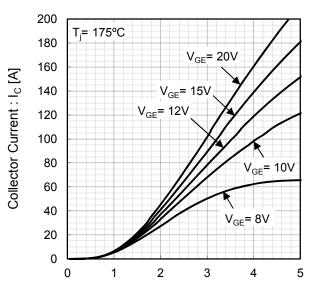


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

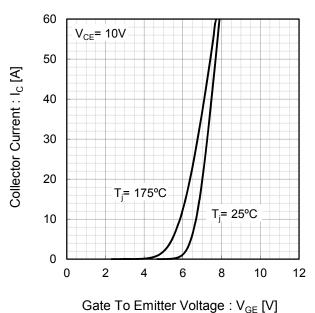
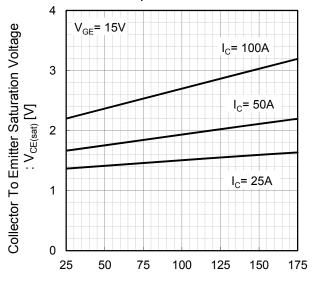


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

### • Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

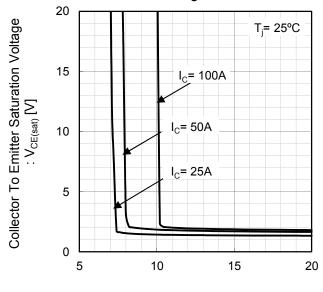
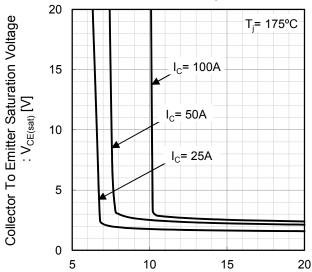


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



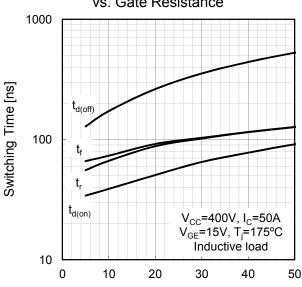
Gate To Emitter Voltage : V<sub>GE</sub> [V]

Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig.11 Typical Switching Time vs. Collector Current

1000  $t_{d(off)}$   $t_{d(off)}$   $t_{d(on)}$   $t_{d(on$ 

Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance :  $R_G[\Omega]$ 

### • Electrical Characteristic Curves

Fig. 13 Typical Switching Energy Losses vs. Collector Current

10  $E_{off}$ 0.1  $E_{off}$   $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{J}$ =175°C

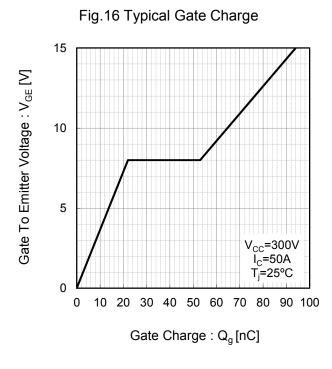
Inductive load

Collector Current :  $I_{C}$  [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=50A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 10 0 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

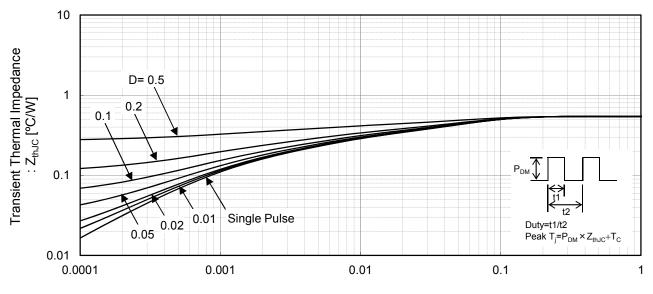
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz  $V_{GE}=0V$ T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]



### • Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

### ●Inductive Load Switching Circuit and Waveform

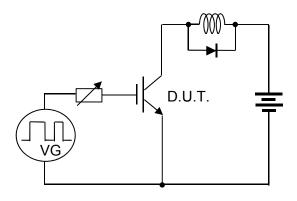


Fig.18 Inductive Load Circuit

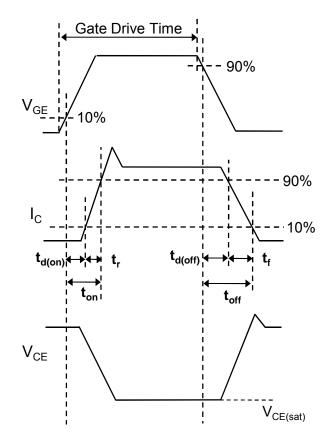


Fig.19 Inductive Load Waveform

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# RGTH00TS65 - Web Page

**Distribution Inventory** 

Part Number	RGTH00TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	450
Packing Type	Bulk
Constitution Materials List	inquiry
RoHS	Yes

单击下面可查看定价,库存,交付和生命周期等信息

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